ABSTRACT

A semiconductor device including a first block word line, and a first channel layer located in the first block word line. the semiconductor device including a source pad connected to the first channel layer and located on the first block word line, and a first drain pad connected to the first channel layer and located on the first block word line. The semiconductor device including a global word line connected to the source pad, and a first local word line connected to the first drain pad.

FIG. 1